

High Speed InGaAs p-i-n Photodiode

Sheet 1 of 1

13PD75LDC-ST, -SMA, -FC, -SC

The 13PD75LDC-ST, an InGaAs photodiode with a 75 μ m-diameter photosensitive region packaged in a TO-46 header and aligned in an AT&T ST active device mount, is a low-dark-current version of the 13PD75-ST intended for high speed and low noise applications. Planar semiconductor design and dielectric passivation provide superior low noise performance. Reliability is assured by hermetic sealing and 100% purge burn-in (200°C, 15 hours, Vr = 20V). The ST receptacle is suitable for bulkhead and PC Board mounting.



Features:

- Planar Structure
- Dielectric Passivation
- 100% Purge Burn-in
- High Responsivity

DEVICE CHARACTERISTICS

Parameters	Test Conditions	Minimum	Typical	Maximum	Units
Operating Voltage				-20	Volts
Dark Current	-5V			0.11	nA
Capacitance	-5V		0.7	0.9	pF
Responsivity	1300nm	0.65	0.8		A/W
Rise/Fall				0.5	ns
Frequency Response	(-3dB)		1.5		GHz

ABSOLUTE MAXIMUM RATINGS

Reverse Voltage	30 Volts
Forward Current	5mA
Reverse Current	5mA
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +85°C
Soldering Temperature	250°C

Sheet 1 of 1

829 Flynn Road, Camarillo, CA 93012 • Phone: (805) 445-4500 • Fax: (805) 445-4502
Email: customerservice@telcomdevices.com • Website: www.telcomdevices.com



Telcom Devices Corp.